

TOSHIBA FIELD EFFECT TRANSISTOR SILICON P CHANNEL MOS TYPE (π -MOSVI)

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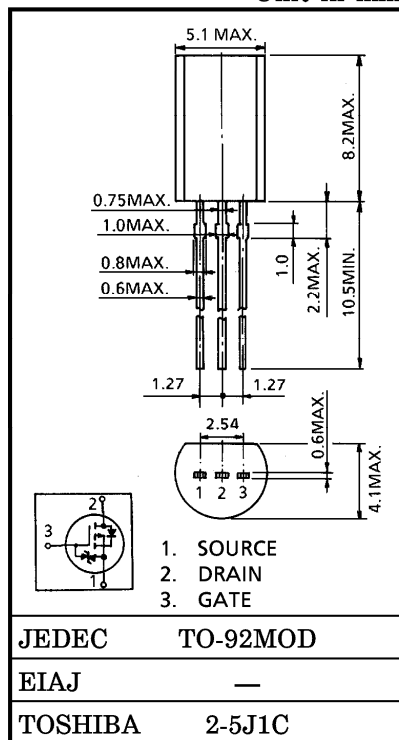
HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS
 CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

INDUSTRIAL APPLICATIONS
 Unit in mm

- Low Drain-Source On Resistance : $R_{DS(ON)} = 0.16 \Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 3.5 S$ (Typ.)
- Low Leakage Current : $I_{DSS} = -100 \mu A$ ($V_{DS} = -50 V$)
- Enhancement-Mode : $V_{th} = -0.8 \sim -2.0 V$
 ($V_{DS} = -10 V, I_D = -1 mA$)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	-50	V
Drain-Gate Voltage ($R_{GS} = 20 k\Omega$)	V_{DGR}	-50	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	DC	I_D	-5 A
	Pulse	I_{DP}	-15 A
Drain Power Dissipation ($T_a = 25^\circ C$)	P_D	0.9	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$



THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	138	$^\circ C/W$

**This transistor is an electrostatic sensitive device.
 Please handle with caution.**

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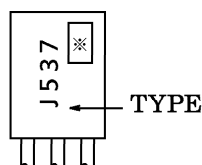
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 10	μA
Drain Cut-off Current		I_{DSS}	$V_{DS} = -50\text{ V}, V_{GS} = 0\text{ V}$	—	—	-100	μA
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$I_D = -10\text{ mA}, V_{GS} = 0\text{ V}$	-50	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = -10\text{ V}, I_D = -1\text{ mA}$	-0.8	—	-2.0	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = -4\text{ V}, I_D = -1.3\text{ A}$	—	0.27	0.34	Ω
			$V_{GS} = -10\text{ V}, I_D = -2.5\text{ A}$	—	0.16	0.19	
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = -10\text{ V}, I_D = -2.5\text{ A}$	1.5	3.5	—	S
Input Capacitance		C_{iss}	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	470	—	pF
Reverse Transfer Capacitance		C_{rss}		—	60	—	
Output Capacitance		C_{oss}		—	210	—	
Switching Time	Rise Time	t_r	<p>$V_{GS} = 0\text{ V}$ (high), -10 V (low) $I_D = -2.5\text{ A}$ $R_L = 10\ \Omega$ $V_{DD} = -25\text{ V}$ $V_{IN}: t_r, t_f < 5\text{ ns}, \text{Duty} \leq 1\%, t_w = 10\ \mu\text{s}$</p>	—	25	—	ns
	Turn-on Time	t_{on}		—	35	—	
	Fall Time	t_f		—	20	—	
	Turn-off Time	t_{off}		—	120	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} = -40\text{ V}, V_{GS} = -10\text{ V}, I_D = -5\text{ A}$	—	18	—	nC
Gate-Source Charge		Q_{gs}		—	13	—	
Gate-Drain (“Miller”) Charge		Q_{gd}		—	5	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	-5	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	-15	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = -5\text{ A}, V_{GS} = 0\text{ V}$	—	—	1.5	V

MARKING



※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)